

Data sheet acquired from Harris Semiconductor SCHS070B – Revised June 2003

CMOS Dual 4-Bit Latch

High-Voltage Types (20-Volt Rating)

CD4508B dual 4-bit latch contains two identical 4-bit latches with separate STROBE, RESET, and OUTPUT DISABLE controls. With the STROBE line in the high state, the data on the "D" inputs appear at the corresponding "Q" outputs provided the DISABLE line is in the low state. Changing the STROBE line to the low state locks the data into the latch. A high on the reset line forces the outputs to a low level regardless of the state of the STROBE input. The outputs are forced to the high-impedance state for bus line applications by a high level on the DISABLE input.

The CD4508B types are supplied in 24-lead hermetic dual-in-line ceramic packages (F3A suffix), 24-lead dual-in-line plastic packages (E suffix), 24-lead small-outline packages (M, M96, and NSR suffixes), and 24-lead thin shrink small-outline packages (PW and PWR suffixes).

The CD4508B is similar to industry type MC14508.

Features:

- Two independent 4-bit latches
- Individual master reset for each 4-bit latch
- 3-state outputs with high-impedance state for bus line applications
- Medium-speed operation: tpHL = tpLH = 70 ns (typ.) at VDD = 10 V and CL = 50 pF
- 100% tested for quiescent current at 20 V
- 5-V, 10-V, and 15-V parametric ratings
- Standardized, symmetrical output characteristics
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (full package-temperature range) =

1 V at VDD = 5 V

2 V at V_{DD} = 10 V

2.5 V at VDD = 15 V

 Meets all requirements of JEDEC Tentative Standard No. 13B,"Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

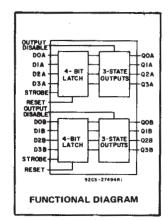
- Buffer storage
- Holding registers
- Data storage and multiplexing

MAXIMUM RATINGS, Absolute-Maximum Values: DC SUPPLY-VOLTAGE RANGE. (VDD)

DO 3011 E. 10E1/1GE 151114E, (1DD)	
Voltages referenced to VSS Terminal)0.5V to +20V	
INPUT VOLTAGE RANGE, ALL INPUTS0.5V to V _{DD} +0.5V	
DC INPUT CURRENT, ANY ONE INPUT	
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -55°C to +100°C	
For T _A = +100°C to +125°C Derate Linearity at 12mW/°C to 200mW	
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR TA = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	
OPERATING-TEMPERATURE RANGE (T _A)55°C to +125°C	
STORAGE TEMPERATURE RANGE (T _{stq})65°C to +150°C	
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max	

RECOMMENDED OPERATING CONDITIONS at $T_A = 25^{\circ}$ C, Except as Noted. For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	V _{DD}	LIM	IITS	
CHARACTERISTIC	(V)	Min.	Max.	UNITS
Supply-Voltage Range (For T _A = Full Package- Temperature Range)		3	18	٧
	5	200	_	
Reset Pulse Width, tW(R)	10	140	_	1
	15	100	_	j
	5	140	_	1
Strobe Pulse Width, tW(st)	10	80	-	
	15	70]
	5	50	_	ns
Setup Time, t _{SU}	10	30	-	
	15	20	_	
	5	0] .
Hold Time, tH	10	0	_	
	15	0	_	



CD4508B Types

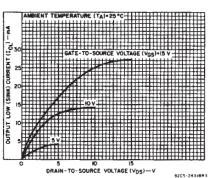


Fig.2 – Typical output low (sink) current characteristics.

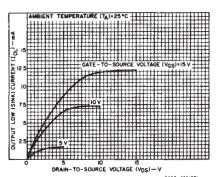


Fig.3 – Minimum output low (sink) current characteristics.

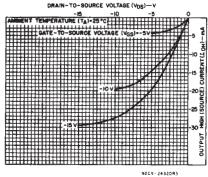


Fig.4 — Typical output high (source) current characteristics.

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STATIC ELECTRICAL CHARACTERISTICS

CHARACTER-	CONE	HOITICA	IS	LIMIT	S AT II	NDICAT	ED TEN	/PERA	UNIT		
12116	Vo (V)	VIN (V)	V _{DD} (V)	-55	-40	+85	+125	Min.	+25 Typ.	Max.	
Quiescent Device	-	0,5	5	5	5	150	150		0.04	5	
Current,		0,10	10	10	10	300	300	_	0.04	10	
IDD Max.		0,15	15	20	20	600	600		0.04	20	μА
		0,10	20	100	100	3000	3000		0.08	100	
Output Low	0.4	0.5	5	0.64	0.61	0.42	0.36	0.51	1		
(Sink) Current	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	-	
IOL Min.	1.5	0,15	15	4.2	4	2.8	2.4	34	6.8	_	
Output High	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	_	mA
(Source) Current, LOH Min.	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2		
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	:	
IOH win.	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-	
Output Voltage:	-	0,5	5		0	.05			0	0.05	-
Low-Level,	_	0,10	10		0	.05		-	0	0.05	
VOL Max.	-	0,15	15		0	.05		-	0	0.05	v .
Output Voltage:	_	0,5	5		4	.95		4.95	5	-	
High-Level, VOH Min.	_	0,10	10	9.95 9.95 10 -						_	,
-AOH Milly	_	0,15	15		14	.95		14.95	15	±(** +	
Input Low	0.5, 4.5		5		1	.5			_	1.5	***
Voltage, V _{IL} Max.	1, 9	-	10			3			112	3	G + 49
AIL May.	1.5,13.5		15			4				4	v
Input High	0.5, 4.5		5			1.5		3.5			•
Voltage,	1, 9		10			7		7			
V _{IH} Min. 1.5,1			15		1	1		11			
Input Current IIN Max.	-	0,18	18	±0.1	±0.1	±1	±1	1	±10 ⁻⁵	±0.1	μΑ
3-State Output Leakage Current IOUT Max.	0,18	0,18	18	±0.4	±0.4	±12	±12		±10-4	±0.4	μΑ

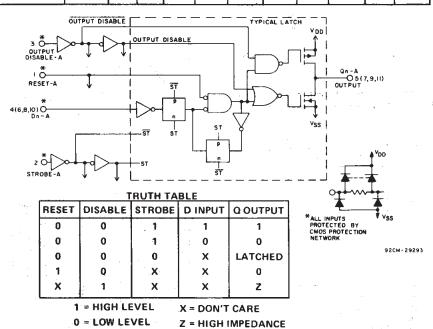


Fig. 7 — Logic diagram (A-Section), 1 of 4 identical latches with common output disable, reset, and strobe.

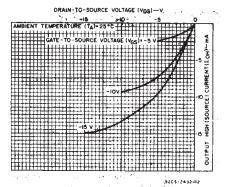


Fig. 4 — Minimum output high (source) current characteristics.

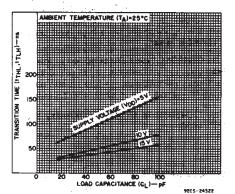


Fig. 5 — Typical transition time as a function of load capacitance.

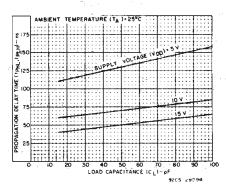


Fig. 6 — Typical propagation delay time as a function of load capacitance (strobe to data out).

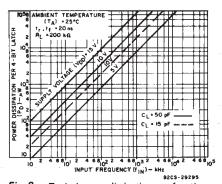
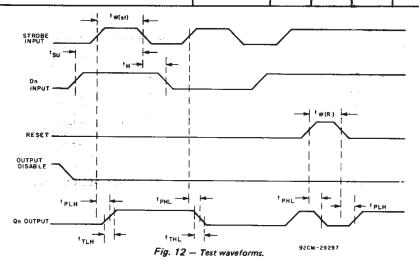


Fig. 8 — Typical power dissipation as a function of frequency.

CD4508B Types

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 k Ω , unless otherwise specified.

CHARACTERISTIC	TEST		LiA	AITS	
CHARACTERISTIC	CONDITIONS	VDD	Тур.	Max.	UNITS
		5	100	200	
Transition Time, tth, ttl	İ	10	50	100	
		15	40	80	
		5	100	200	1
Minimum Reset Pulse Width, tW(R)	İ	10	70	140	<u> </u>
		15	50	100	
		5	70	140	1
Minimum Strobe Pulse Width, tW(st)		10	.40	80	
	İ	15	35	70	
		5	25	50	1
Minimum Setup Time, t _{SU}		10	15	30	
		15	10	20	
		5	0	0	
Minimum Hold Time, t _H		10	0	0	}
		15	0	0	
Propagation Delay Times: tpHL,tpLH		5	130	260	
Strobe to Data Out		10	70	140	
4	ļ	15	50	100	ns
		5	105	210	
Data In to Data Out		10	60	120	7
		15	45	90	
	İ	5	90	180	
Reset to Data Out	1	10	50	100	
		15	40	80	
20th Burney Co. D. L. Ti		5	90	180	
3-State Propagation Delay Times:		10	50	100	
Output High to High Impedance,tpHZ		15	35	70	
		5	90	180	
High Impedance to Output High, tpZH		10	50	100	
		15	35	70	
	111	5	90	180	
Output Low to High Impedance, tpLZ		10	50	100	
		15	35	70	
		5	90	180	
High Impedance to Output Low, tpZL		10	50	100	
The state of the s		15	35	70	
Input Capacitance, CIN	Any Input	-	5	7.5	pF
			. 1		



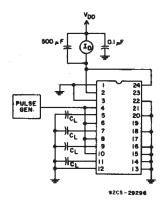


Fig.9 - Power dissipation test circuit.

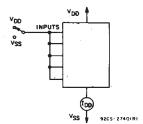


Fig. 10 — Quiescent device current test circuit.

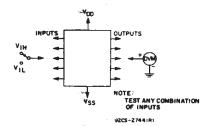


Fig. 11 - Input voltage test circuit.

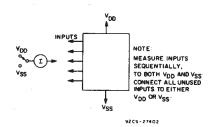


Fig. 13 - Input current test circuit.

CD4508B Types

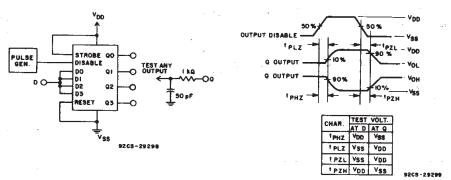


Fig. 14 - Output disable test circuit and waveforms.

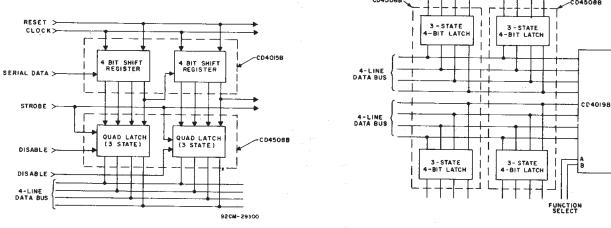
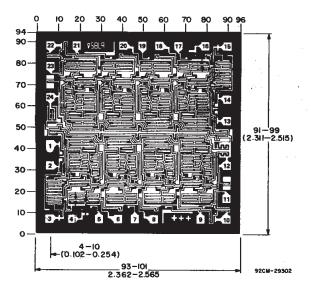


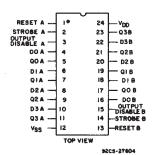
Fig. 15 - Bus register.



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch) .

Chip dimensions and pad layout for CD4508B.

Fig.16 — Dual multiplexed bus register with function select.



92CM - 29301

DATA BUS

TERMINAL ASSIGNMENT





9-Mar-2021

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
CD4508BD3	ACTIVE	CDIP SB	JD	24	1	Non-RoHS & Non-Green	(6) SNPB	N / A for Pkg Type	-55 to 125	CD4508BD/3	Samples
CD4508BF3A	ACTIVE	CDIP	J	24	1	Non-RoHS & Non-Green	Call TI	N / A for Pkg Type	-55 to 125	CD4508BF3A	Samples
CD4508BM	ACTIVE	SOIC	DW	24	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4508BM	Samples
CD4508BM96	ACTIVE	SOIC	DW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4508BM	Samples
CD4508BNSR	ACTIVE	so	NS	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4508B	Samples
CD4508BPW	ACTIVE	TSSOP	PW	24	60	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CM508B	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



PACKAGE OPTION ADDENDUM

9-Mar-2021

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OTHER QUALIFIED VERSIONS OF CD4508B, CD4508B-MIL:

Catalog: CD4508B

Military: CD4508B-MIL

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD4508BM96	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
CD4508BNSR	SO	NS	24	2000	330.0	24.4	8.3	15.4	2.6	12.0	24.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD4508BM96	SOIC	DW	24	2000	350.0	350.0	43.0
CD4508BNSR	SO	NS	24	2000	367.0	367.0	45.0

PACKAGE MATERIALS INFORMATION

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TUBE



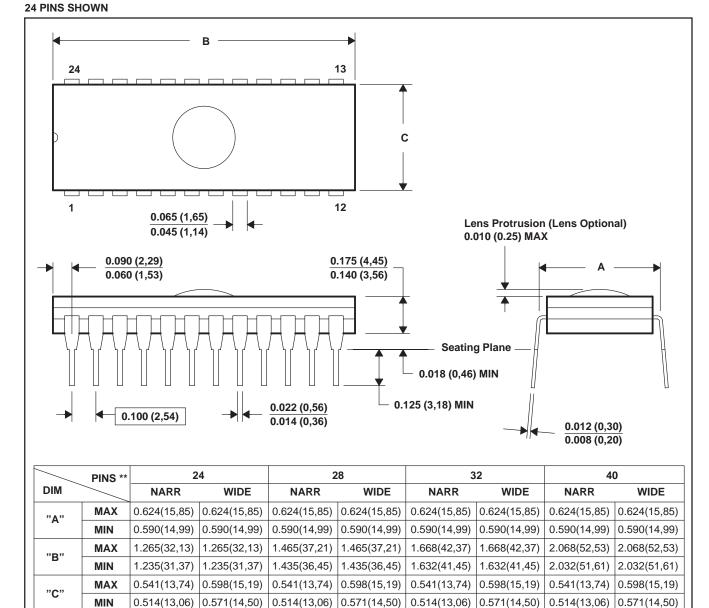
*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CD4508BM	DW	SOIC	24	25	506.98	12.7	4826	6.6
CD4508BPW	PW	TSSOP	24	60	530	10.2	3600	3.5

4040084/C 10/97

J (R-GDIP-T**)

CERAMIC DUAL-IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. Window (lens) added to this group of packages (24-, 28-, 32-, 40-pin).
- D. This package can be hermetically sealed with a ceramic lid using glass frit.
- E. Index point is provided on cap for terminal identification.





SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



MECHANICAL DATA

NS (R-PDSO-G**)

14-PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

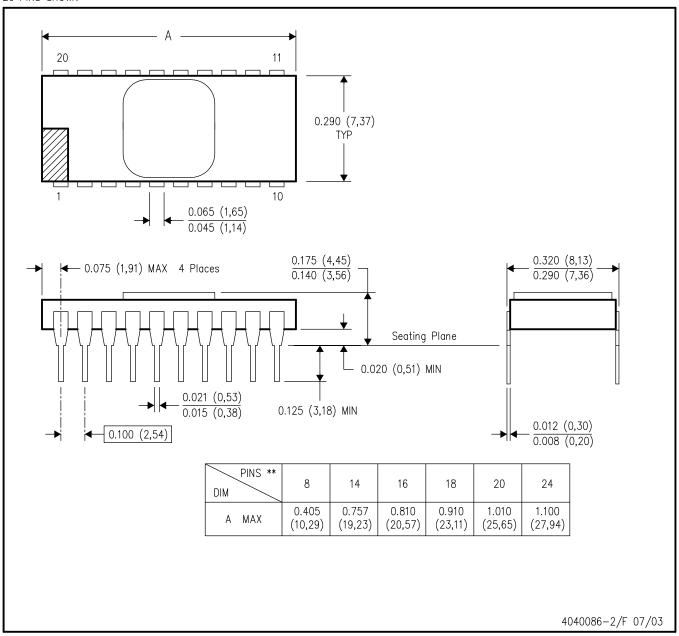
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



JD (R-CDIP-T**)

CERAMIC SIDE-BRAZE DUAL-IN-LINE PACKAGE

20 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a metal lid.
- D. The terminals are gold plated.
- E. Falls within MIL STD 1835 CDIP2 T8, T14, T16, T18, T20 and T24 respectively.



DW (R-PDSO-G24)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AD.



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